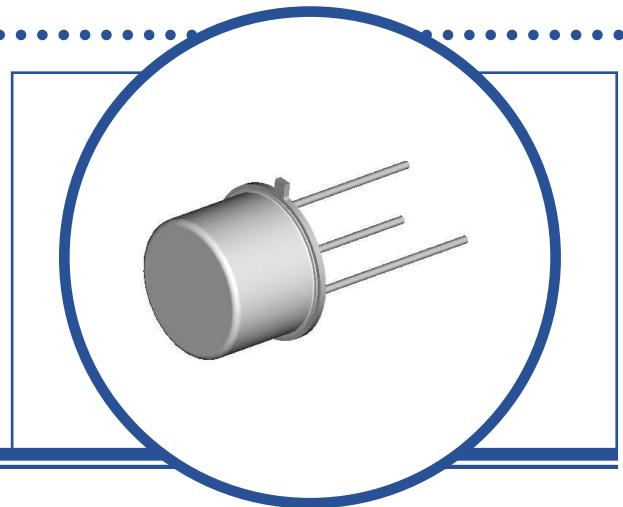


GENERAL PURPOSE SILICON NPN TRANSISTOR

2N697

- Hermetic TO39 (TO-205AD) Metal Package.
- Ideally suited for General Purpose Applications
- Screening Options Available



ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ unless otherwise stated)

V_{CBO}	Collector – Base Voltage		60V
V_{CER}	Collector – Emitter Voltage		40V
V_{EBO}	Emitter – Base Voltage		5.0V
P_D	Total Power Dissipation at	$T_A = 25^\circ\text{C}$	600mW
		Derate Above 25°C	4.0mW/ $^\circ\text{C}$
P_D	Total Power Dissipation at	$T_C = 25^\circ\text{C}$	2.0W
		Derate Above 25°C	13.3mW/ $^\circ\text{C}$
T_J	Junction Temperature Range		-65 to $+200^\circ\text{C}$
T_{stg}	Storage Temperature Range		-65 to $+200^\circ\text{C}$

THERMAL PROPERTIES

Symbols	Parameters	Max.	Units
$R_{\theta JA}$	Thermal Resistance, Junction To Ambient	290	$^\circ\text{C}/\text{W}$
$R_{\theta JC}$	Thermal Resistance, Junction To Case	88	$^\circ\text{C}/\text{W}$

Semelab Limited reserves the right to change test conditions, parameter limits and package dimensions without notice. Information furnished by Semelab is believed to be both accurate and reliable at the time of going to press. However Semelab assumes no responsibility for any errors or omissions discovered in its use. Semelab encourages customers to verify that datasheets are current before placing orders.



SILICON PLANAR EPITAXIAL NPN TRANSISTOR 2N697

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise stated)

Symbols	Parameters	Test Conditions	Min.	Typ.	Max.	Units
$V_{(BR)CER}^{(1)}$	Collector-Emitter Breakdown Voltage	$I_C = 10\text{mA}$ $R_{BE} = 10\Omega$	40			V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	$I_C = 100\mu\text{A}$ $I_E = 0$	60			
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E = 100\mu\text{A}$ $I_C = 0$	5.0			
I_{CBO}	Collector Cut-Off Current	$V_{CB} = 30\text{V}$ $I_E = 0$			1.0	μA
			$T_A = 150^\circ\text{C}$		100	
$V_{CE(sat)}^{(1)}$	Collector-Emitter Saturation Voltage	$I_C = 150\text{mA}$ $I_B = 15\text{mA}$			1.5	V
$V_{BE(sat)}^{(1)}$	Base-Emitter Saturation Voltage	$I_C = 150\text{mA}$ $I_B = 15\text{mA}$			1.3	
$h_{FE}^{(1)}$	Forward-current transfer ratio	$I_C = 150\text{mA}$ $V_{CE} = 10\text{V}$	40		120	

DYNAMIC CHARACTERISTICS

$ h_{fe} $	Small signal forward-current transfer ratio	$I_C = 50\text{mA}$ $V_{CE} = 10\text{V}$ $f = 20\text{MHz}$	2.5			
C_{obo}	Output Capacitance	$V_{CB} = 10\text{V}$ $I_E = 0$ $f = 1.0\text{MHz}$			35	pF

Notes

(1) Pulse Width $\leq 300\mu\text{s}$, $\delta \leq 2\%$

MECHANICAL DATA

Dimensions in mm (inches)

TO39 (TO-205AD) Underside View

Pin 1
Emitter

Pin 2
Base

Pin 3
Collector

